

MEDEA+ Efforts on Maskless Lithography

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Maskless Meeting

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MEDEA+ Program – Overview

- Medea+ Maskless Lithography Projects**
- European Advisory Board on Maskless Lithographies**
- Maskless Domains**
- A Business Model for Maskless Lithography?**
- Conclusion**

Medea+ Projects

- ❑ **~50 projects running or completed
(~20 new proposals submitted)**
- ❑ **⇒ 22 Technology projects**
- ❑ **⇒ 7 Lithography projects**
- ❑ **⇒ 2 Maskless Lithography projects**

MEDEA+ Projects on CP-ML2

□ T408 Mapper

- **Objective: C&F Mapper tool**
- **Coordination: Mapper Lithography**
- **Partners: Philips ETG, Philips Research, Philips Semiconductors, IMEC**
- **Duration: 2003-2005**

□ T409 Projection-ML2

- **Objective: C&F of PML2 tool**
- **Coordination: Leica Microsystems**
- **Partners: IMS Nanofabrication, IMS Jena, FhG ISiT, FhG HHI, FhG IOF, CEA LETI, EQUIcon, IMS Chips, Infineon Technologies, STMicroelectronics, Philips Semiconductors**
- **Duration: 2004-2006**

European Advisory Board for Maskless Lithographies

Membership: suppliers and users

- ASML
- Leica Microsystems
- Mapper Lithography
- Infineon Technologies
- Philips Semiconductors
- STMicroelectronics
- MEDEA+

European Advisory Board for Maskless Lithographies: Charter

□ **Steering of European Maskless Lithography Program**

➤ **Maskless Masterplan**

- Provide benchmark for projects
- Status review of maskless lithography program
- Assessment of expectations & possibilities

➤ **Business model update, mask cost structure**

- Continue supplier-user exchange

➤ **Coordination of activities within and between Maskless projects**

□ **European maskless litho contact body**

➤ **Contacts with other consortia**

➤ **Press info (in cooperation with Medea+)**

Maskless Lithography Masterplan

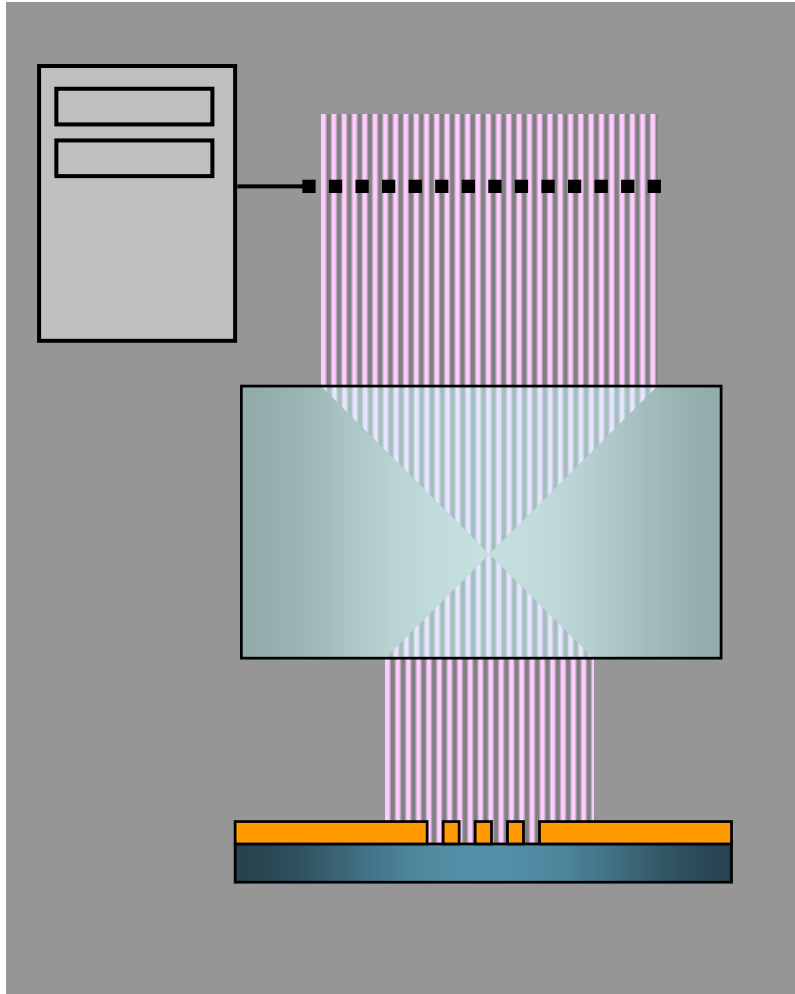
□ Benchmark MEDEA+ program

- Tool capability (5-10 wph)
- Concept design: potential > 1 wph
- Potential tools for 2007
- Target: 45 nm half pitch

□ User requirements

- Applications and expectations for maskless lithography
- Distinguish:
 - Device engineering (resolution driven)
 - Prototyping (cycle-time driven)
 - (Low) volume production (cost driven)

Maskless Lithographies: common features



- Optical or particle-based
- Multibeam
(10 – 20,000)
- Beam modulation:
deflection, scattering,
blanking
(MEMS technology)
- High data rate (>10 Gb/s)
- Various designs under
development:
Tools in 2007

Maskless Lithography Domains

- A. Device engineering: *Resolution driven***
High-resolution patterning for advanced device architecture validation
R&D phase for technology node n+2 (i.e. 45 nm hp)
- B. Prototyping: *Cycle-time driven***
Patterning for design validation of new products
After validation, volume production will start
- C. Low volume production: *Cost-reduction driven***

All domains should allow mix and match with scanners

Device Engineering

- ❑ **Throughput requirement: >0.2 wph**
(capability for different wafer sizes: 200, 300 mm)
- ❑ **# critical levels: ~15 - >20**
- ❑ **Overlay accuracy:**
23 nm @ 65 nm hp
18 nm @ 45 nm hp
- ❑ **Design grid 5 nm for 65 nm**
(1 nm OPC grid @ poly)

Prototyping

- Throughput requirement: >5wph (300 mm)**
- # critical levels: ~10-15**
- Overlay accuracy:
32 nm @ 90 nm hp**
- # wafers per design verification: 35**

Low Volume Production

- Throughput requirement: > 10 wph (300 mm)
- # critical levels: <10
- Overlay accuracy:
35 nm (120 nm / 90 nm nodes)
- # wafers/product: ~1500

A Business Model for Maskless Lithography?

ML2 in the wafer fab

Compare:

- Maskless Lithography
(various concepts: A, B, C)
- E-beam direct write (EBDW)
- Mask-based: Multi-layer reticles (MLR)

The wafer fab does not pay for masks!

→ ML2 is more expensive for the fab

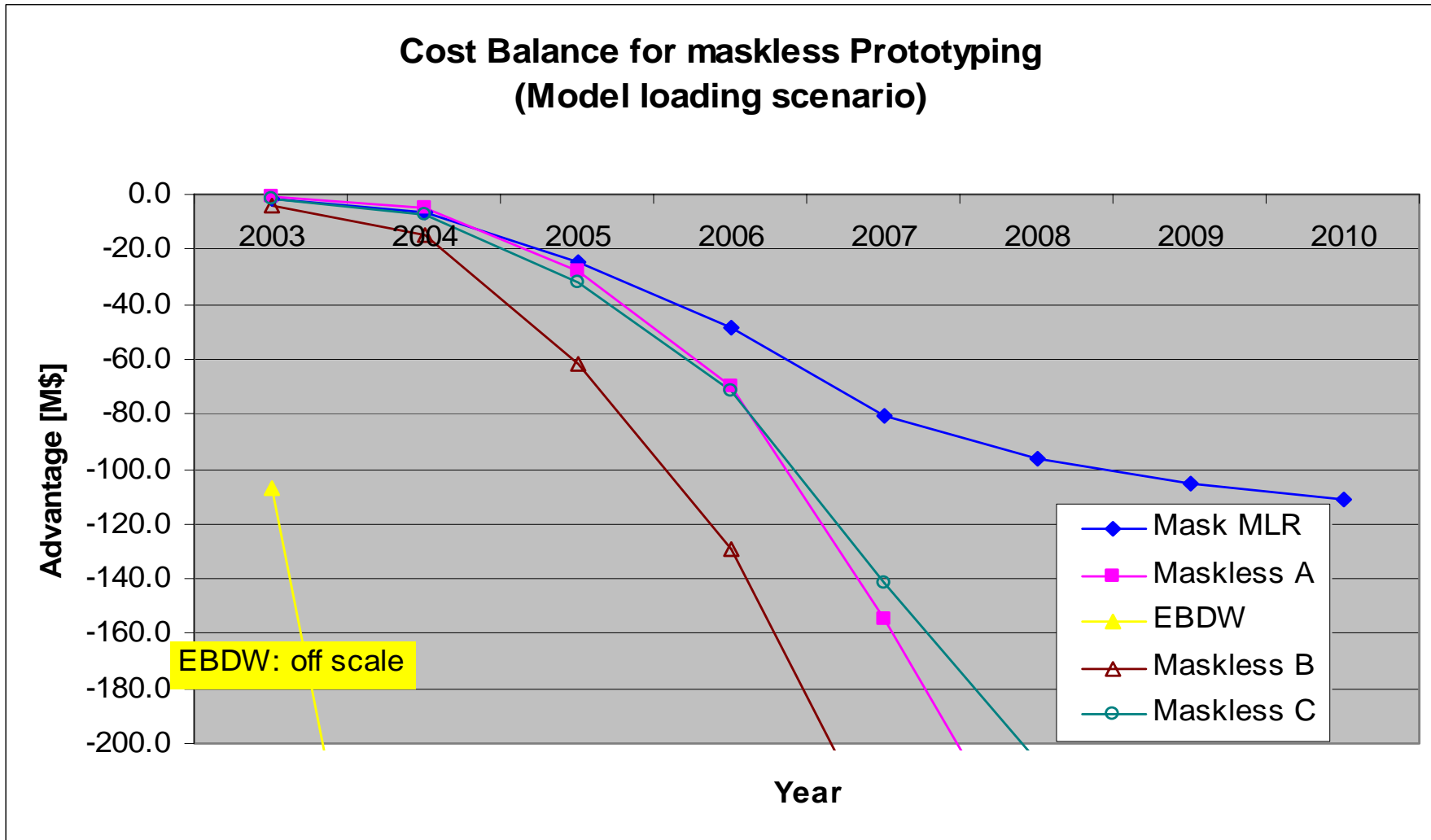
Business model for maskless lithography: inputs

- Benefit derives from low or no mask costs**
- Cost is created by low throughput and dedicated tools**
 - Depreciation of tool & associated track to be taken into account
 - Fab overhead: foot print area
- Prototyping characteristics**
 - Success rate
 - Optical requalification costs
 - Mask respins
- Possible additional costs for maskless**
 - Cost for different dataprep procedures for maskless?
 - Differences in chemicals/maintenance/operating costs per wafer
 - Additional CoO for two litho lines (prototyping & volume production in fab)
 - Optical maskless: match tool for mask-based imaging (193, 248 nm)

Differential CoO for Maskless Lithography Equipment Parameters

Item	MaskBased	Mask MLR	EBDW	Maskless A	Maskless B	Maskless C
Tool cost [M\$]	25	25	10	25	10	15
Track cost [M\$]	5	5	2	2	2	2
Depreciation time [yr]	5	5	5	5	5	5
Depreciation / year [M\$/yr]	6	6	2.4	5.4	2.4	3.4
Floorspace Expo [m ²]	10	10	4	10	4	4
Floorspace Track [m ²]	12	12	8	8	8	8
Floorspace total [m ²]	22	22	12	18	12	12
Floorspace price [\$/m ²]	5000	5000	5000	5000	5000	5000
Floorspace contribution/year [M\$/yr]	0.11	0.11	0.06	0.09	0.06	0.06
Floorspace ratio w.r.t. mask	1.00	1.00	0.55	0.82	0.55	0.55
Nominal throughput [wph]	90	23	0.2	10	5	10
Uptime [%]	80	80	80	80	80	80
Utilization [%]	95	95	95	95	95	95

Is maskless lithography more cost-effective?



Maskless lithography for prototyping: Preliminary conclusions

- Maskless prototyping is not (yet) cost-effective for the fab**
 - **Impact on fab output cost is larger than gain by 'no mask cost'.**
 - **Throughput increase for maskless has only limited effect**
 - **From a cost/prototype perspective, use of multi-layer reticles (MLR) seems most attractive**
- However, maskless lithography may shorten development time**
- Flexibility – not cost reduction – is a primary driver for maskless lithography**